



Figure 1: (a)-(d) AFM images showing how the surface morphology changes as a function of increasing InGaAs deposition in monolayers (ML). (e) SEM image of a larger surface area showing how the InGaAs nanostructures preferentially decorate the characteristic triangular features of the (111) surface. (f) Cross-sectional TEM image showing the strain contrast and defect-free nature of an InGaAs QD layer within the GaSb(111)A matrix. (g) PL emission spectra from three InGaAs/GaSb(111)A QD samples grown with varying deposition amounts.